



PSMN021-100YL

N-channel 100 V, 21 mΩ logic level MOSFET in LFPK56

2 June 2016

Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

2. Features and benefits

- Advanced TrenchMOS provides low $R_{DS(on)}$ and low gate charge
- Logic level gate operation
- Avalanche rated, 100 % tested
- LFPK provides maximum power density in a Power SO8 package

3. Applications

- Synchronous rectification in power supply equipment
- Chargers & adaptors with $V_{out} < 10$ V
- Fast charge & USB-PD applications
- Battery powered motor control
- LED lighting & TV backlight

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	100	V
I_D	drain current	$V_{GS} = 5\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2	-	-	49	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1	-	-	147	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 5\text{ V}$; $I_D = 15\text{ A}$; $T_j = 25\text{ °C}$; Fig. 11	-	17.4	22	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$I_D = 15\text{ A}$; $V_{DS} = 80\text{ V}$; $V_{GS} = 5\text{ V}$; $T_j = 25\text{ °C}$; Fig. 13 ; Fig. 14	-	13.3	-	nC

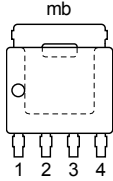
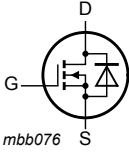


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LFAK56; Power-SO8 (SOT669)</p>	
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN021-100YL	LFAK56; Power-SO8	Plastic single-ended surface-mounted package (LFAK56; Power-SO8); 4 leads	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN021-100YL	21L100

8. Limiting values

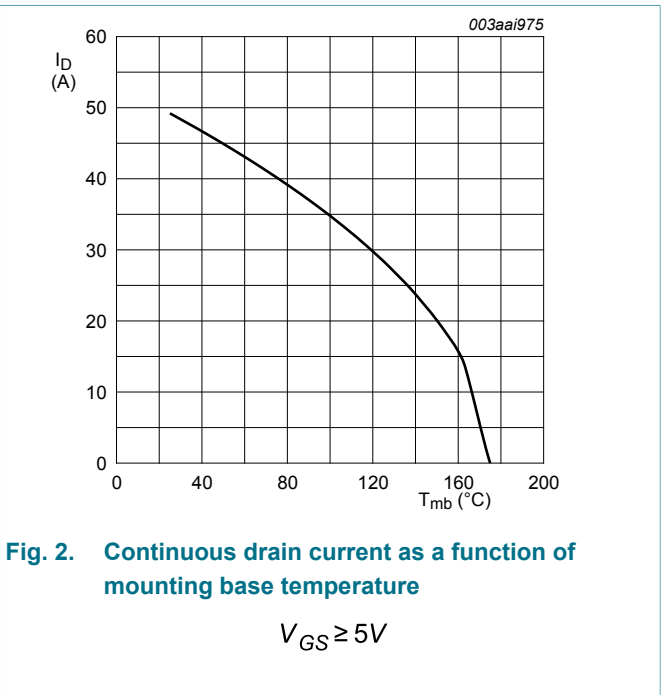
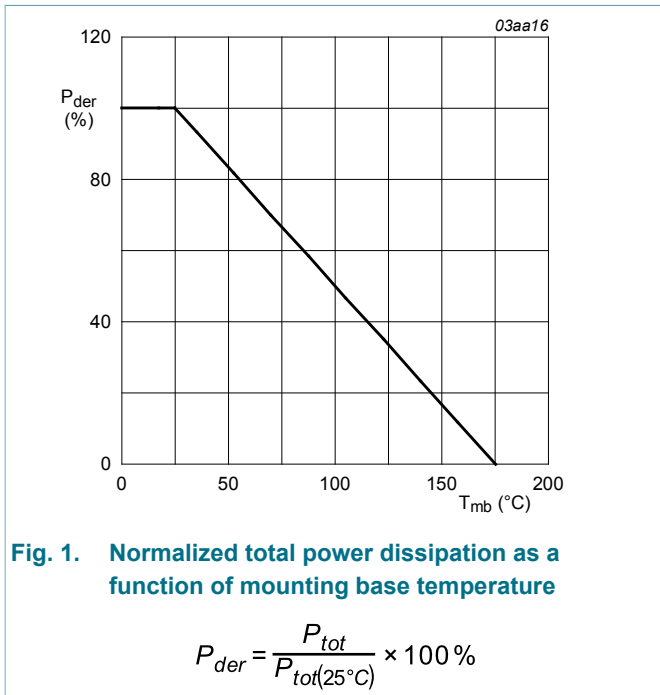
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1	-	147	W
I_D	drain current	$V_{GS} = 5\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2	-	49	A
		$V_{GS} = 5\text{ V}$; $T_{mb} = 100\text{ °C}$; Fig. 2	-	35	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; Fig. 3	-	197	A
T_{stg}	storage temperature		-55	175	°C

Symbol	Parameter	Conditions	Min	Max	Unit
T _j	junction temperature		-55	175	°C
Source-drain diode					
I _S	source current	T _{mb} = 25 °C	-	49	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C	-	197	A
Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 49 A; V _{sup} ≤ 100 V; R _{GS} = 50 Ω; V _{GS} = 5 V; T _{j(init)} = 25 °C; unclamped; Fig. 4	[1][2]	-	80.8 mJ

- [1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [2] Refer to application note AN10273 for further information.



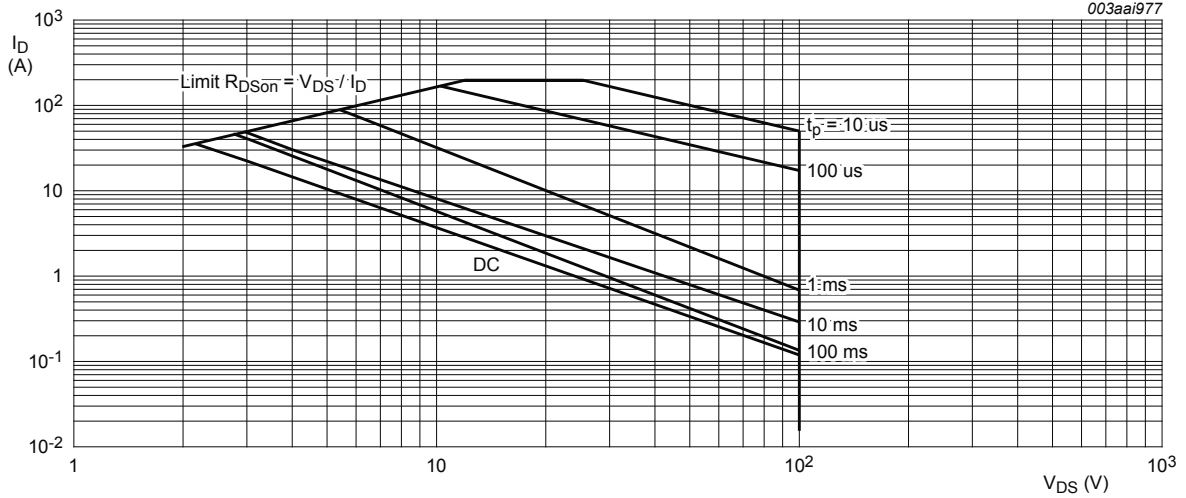


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^\circ C$; I_{DM} is a single pulse

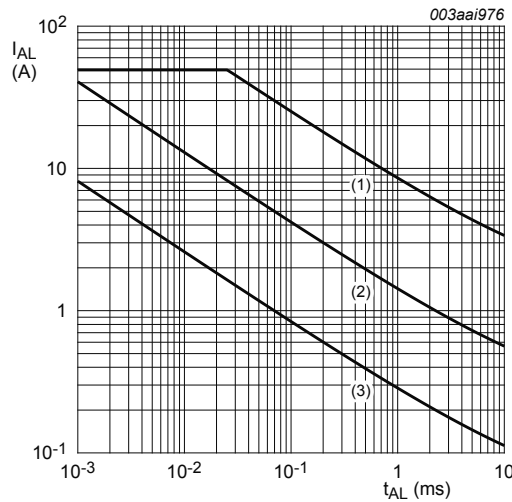


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1) $T_j(\text{init}) = 25^\circ C$; (2) $T_j(\text{init}) = 150^\circ C$; (3) Repetitive Avalanche

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	1.02	K/W

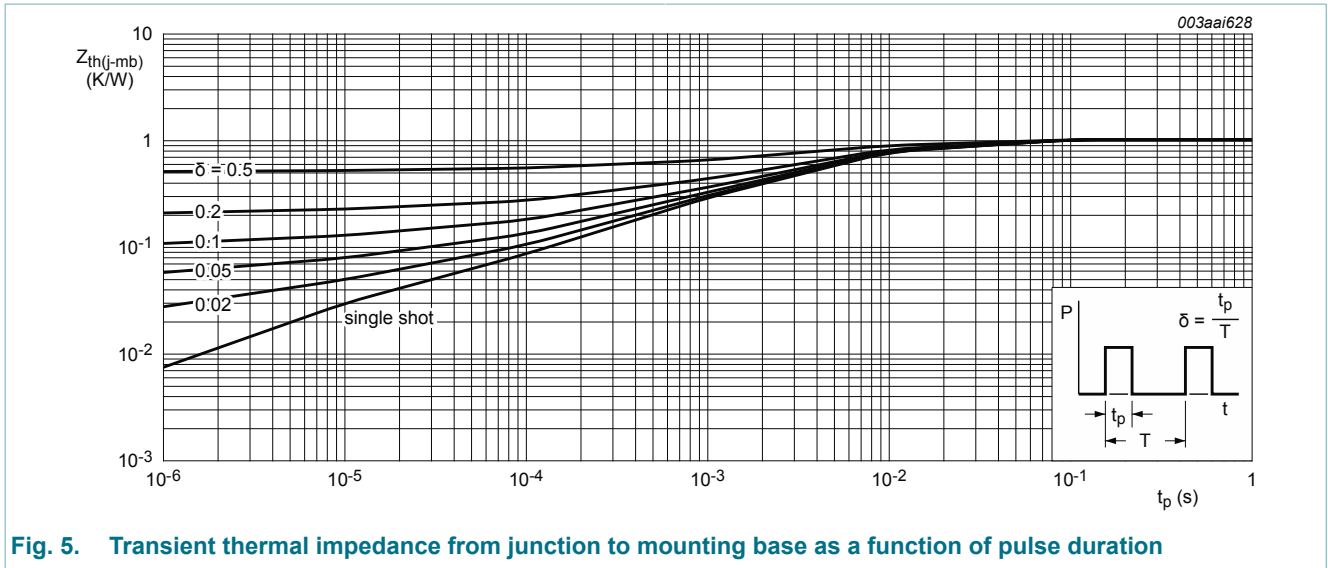


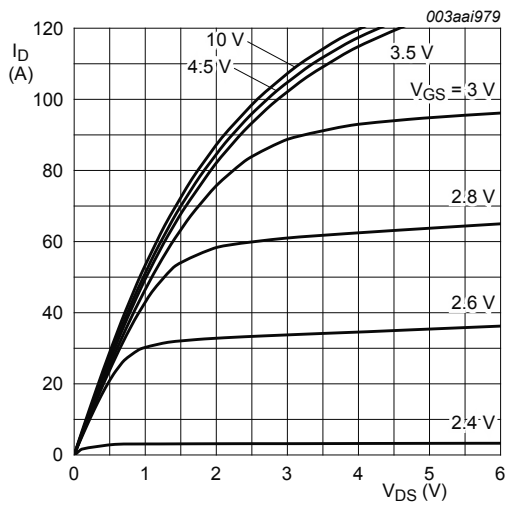
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	100	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C$; Fig. 9 ; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ C$; Fig. 9	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ }^\circ C$; Fig. 9	0.5	-	-	V
I_{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ C$	-	-	500	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	0.04	10	μA
I_{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ C$; Fig. 11	-	17.4	22	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ C$; Fig. 11	-	16.8	21.5	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ }^\circ C$; Fig. 12 ; Fig. 11	-	-	60.7	mΩ
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 15 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ }^\circ C$; Fig. 13 ; Fig. 14	-	65.6	-	nC
		$I_D = 15 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V}; T_j = 25 \text{ }^\circ C$; Fig. 13 ; Fig. 14	-	35.8	-	nC
Q_{GS}	gate-source charge	$T_j = 25 \text{ }^\circ C$; Fig. 13 ; Fig. 14	-	6.2	-	nC

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Q_{GD}	gate-drain charge		-	13.3	-	nC
C_{iss}	input capacitance	$V_{DS} = 25\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ }^\circ\text{C}; \text{Fig. 15}$	-	3480	4640	pF
C_{oss}	output capacitance		-	212	254	pF
C_{rss}	reverse transfer capacitance		-	130	178	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 80\text{ V}; R_L = 5\text{ }^\Omega; V_{GS} = 5\text{ V}; R_{G(ext)} = 5\text{ }^\Omega; T_j = 25\text{ }^\circ\text{C}$	-	15.8	-	ns
t_r	rise time		-	32.3	-	ns
$t_{d(off)}$	turn-off delay time		-	53.4	-	ns
t_f	fall time		-	31.1	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 15\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}; \text{Fig. 16}$	-	0.82	1.2	V
t_{rr}	reverse recovery time	$I_S = 15\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	38.2	-	ns
Q_r	recovered charge		-	66	-	nC



$T_j = 25\text{ }^\circ\text{C}; t_p = 300\text{ }\mu\text{s}$

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

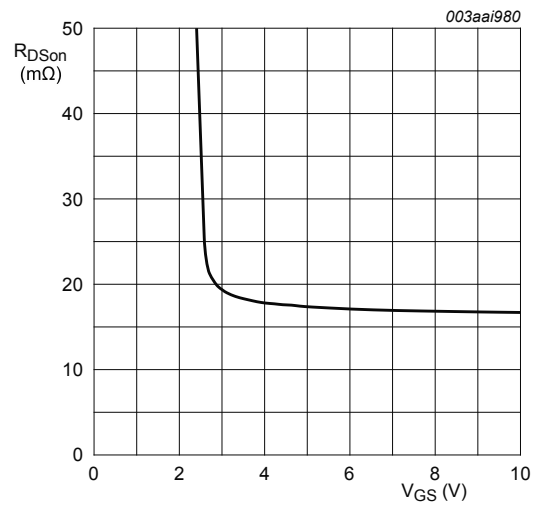


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\text{ }^\circ\text{C}; I_D = 15\text{ A}$

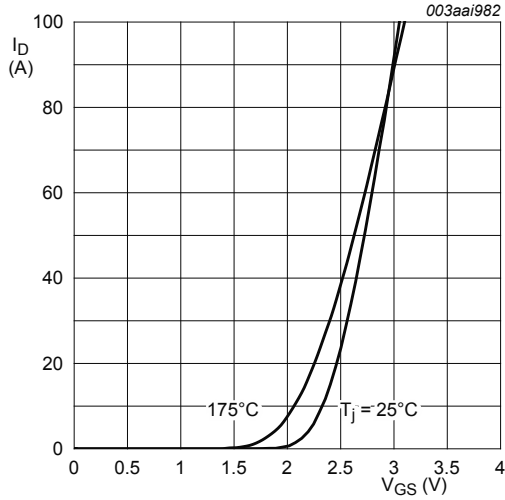


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10V$



Fig. 9. Gate-source threshold voltage as a function of junction temperature

$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

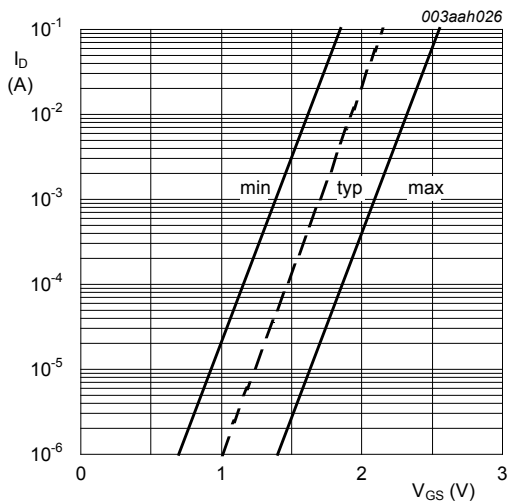
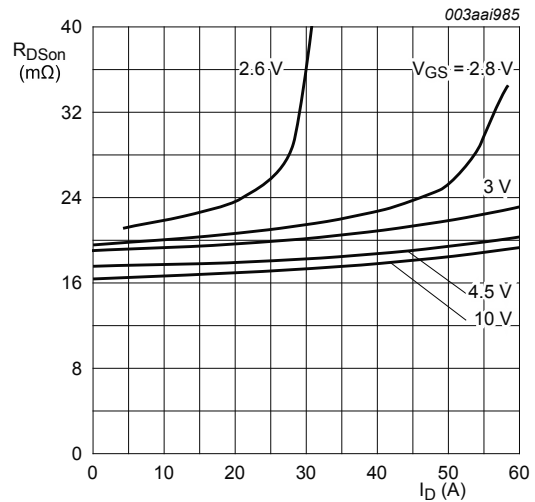


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25^\circ C; V_{DS} = 5V$



$T_j = 25^\circ C; t_p = 300 \mu s$

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

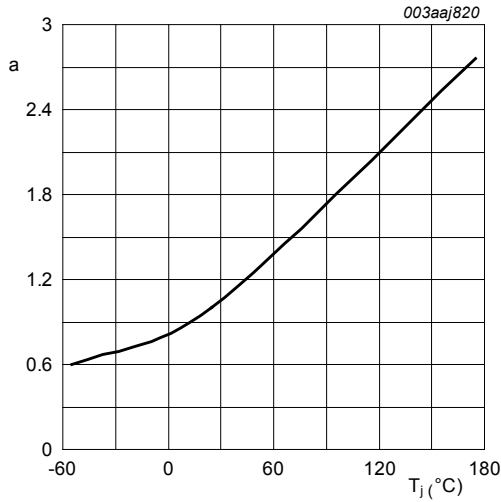


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}C)}$$

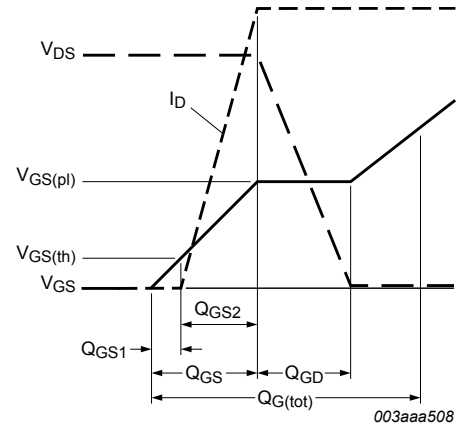


Fig. 13. Gate charge waveform definitions

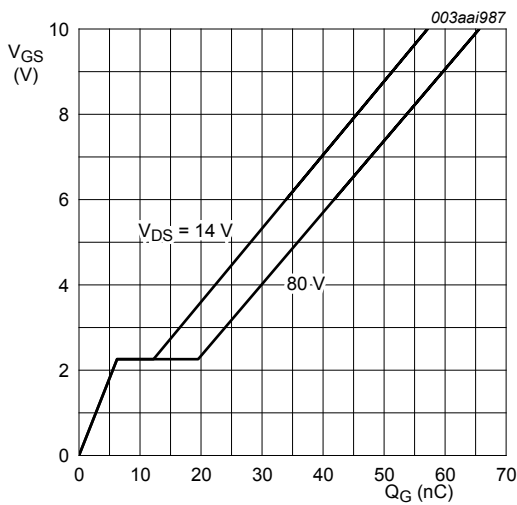


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 15A$$

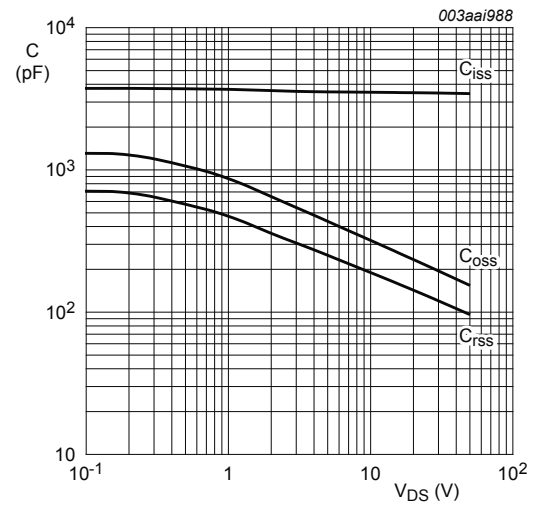


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

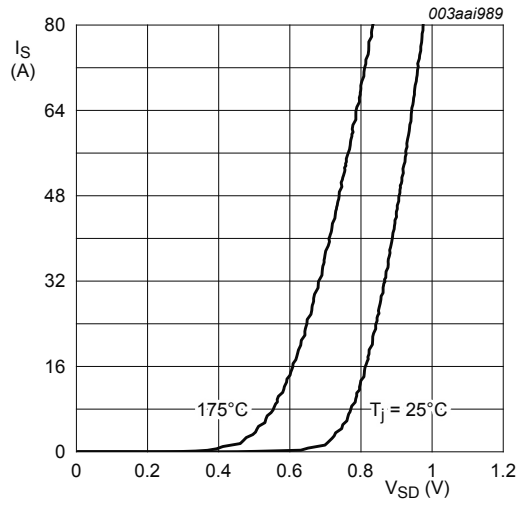


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

11. Package outline



Fig. 17. Package outline LFAK56; Power-SO8 (SOT669)

12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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